
HN62435 Series

262144-word $\times$ 16-bit/524288-word $\times$ 8-bit CMOS Mask
Programmable ROM

HITACHI

ADE-203-472B (Z)

Rev. 2.0

Jun. 11, 1997

Description

The Hitachi HN62435 series is a 4-Mbit CMOS mask programmable ROM organized either as 262144-word $\times$ 16-bit or as 524288-word $\times$ 8-bit. As it has realized high speed access 120 ns, it is the most suitable to the program and data memory for micro computer system. It has package variations of standard 40-pin plastic DIP, standard 40-pin plastic SOP and standard 44-pin plastic TSOPII.

Features

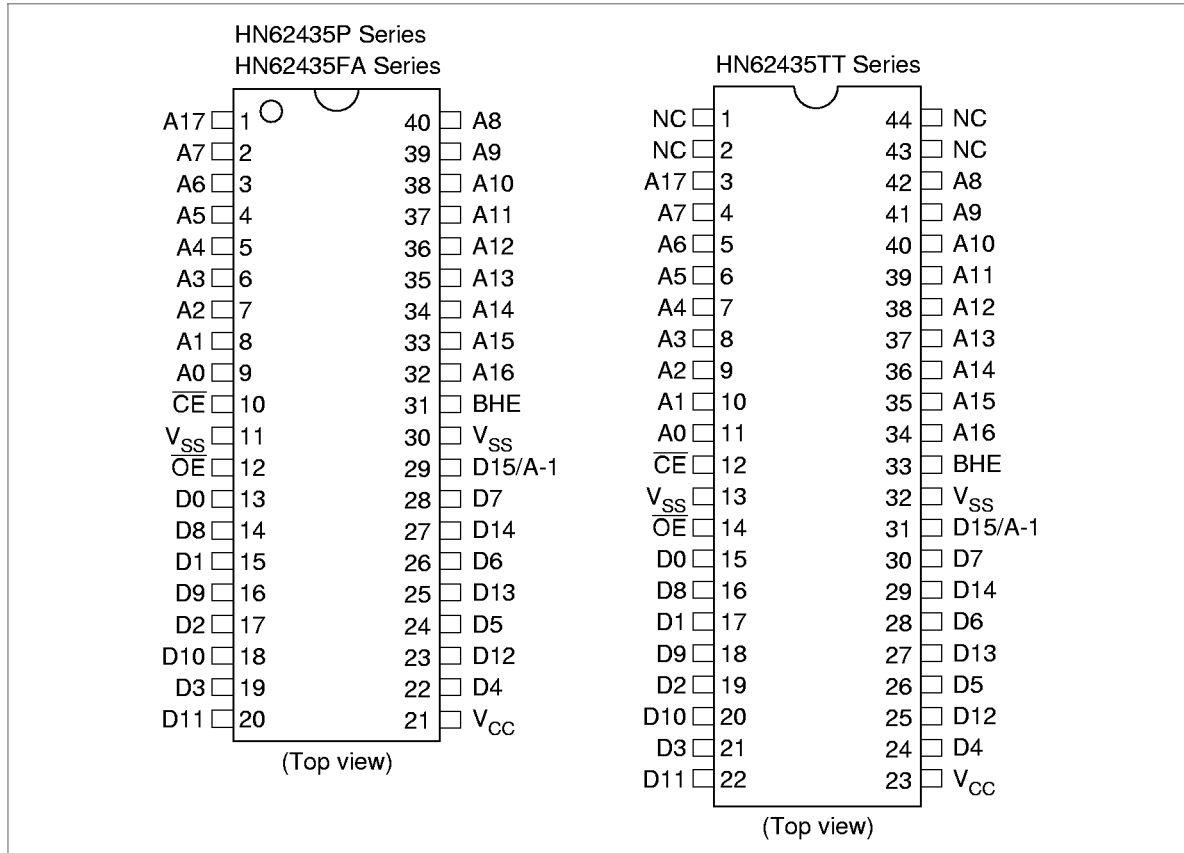
- Single 5 V supply: 5.0 V $\pm$ 10%
- Access time: 120 ns (max)
- Power dissipation
 - Active: 275 mW (max)
 - Standby: 165 μ W (max)
- Byte-wide or word-wide data organization with byte/word selection (BHE)
- Three-state data output for wired or-tying
- Directly TTL compatible all inputs and outputs

Ordering Information

Type No.	Access time	Package
HN62435P-12	120 ns	600 mil 40-pin plastic DIP (DP-40)
HN62435FA-12	120 ns	525 mil 40-pin plastic SOP (FP-40D)
HN62435TT-12	120 ns	400 mil 44-pin plastic TSOPII (TTP-44D)

HN62435 Series

Pin Arrangement



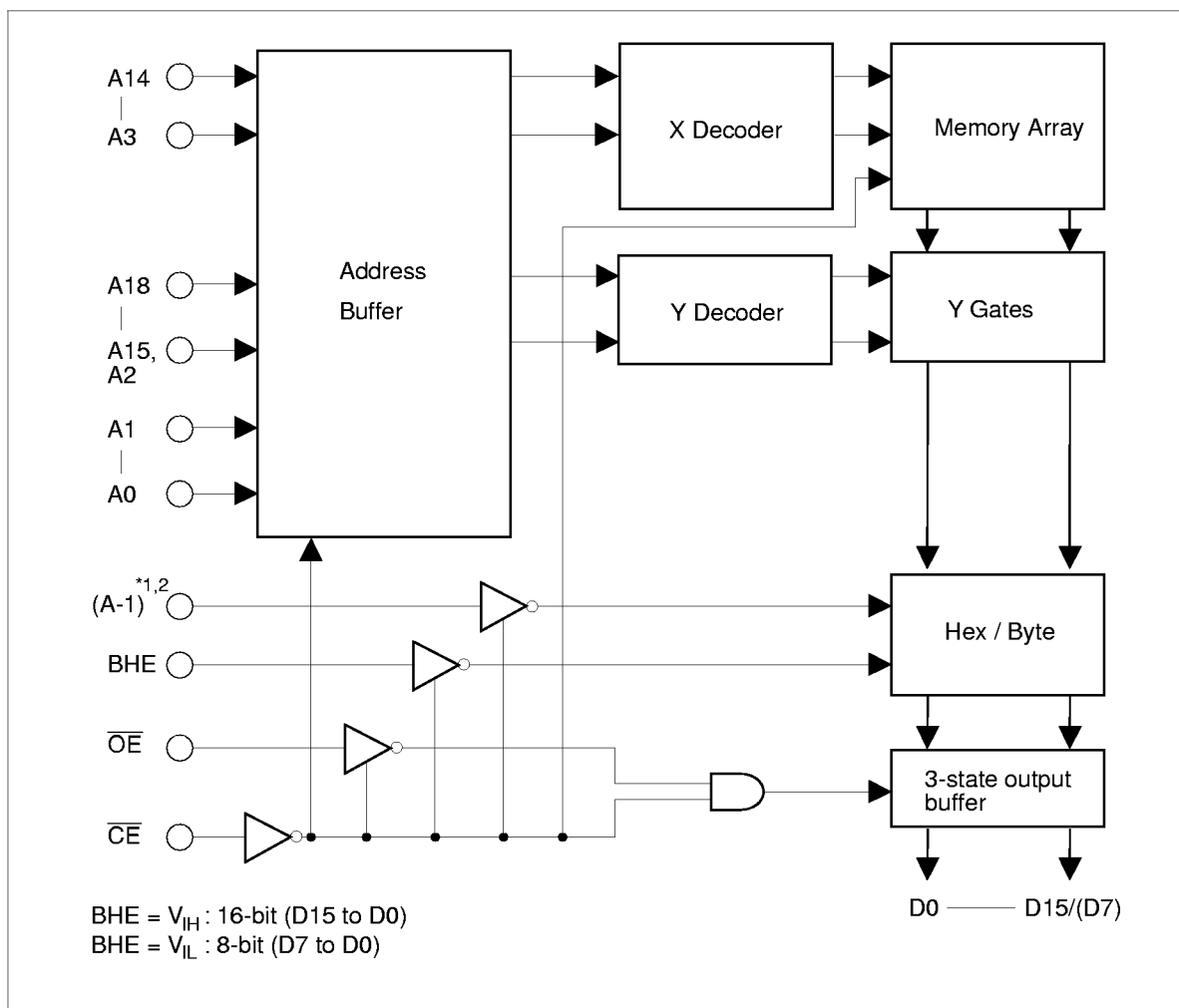
Pin Description

Pin name	Function
A-1, A0 to A17	Address input
D0 to D15	Data output
$\overline{OE}$	Output enable
$\overline{CE}$	Chip enable
BHE	Byte/word selection
V_{CC}	Power supply
V_{SS}	Ground
NC	No connection

Block Diagram

Notes: 1. A-1 is least significant address.

2. When BHE is 'low', D14 to D8 goes the high impedance state, and D15 should be A-1.



Operation Table

Mode	$\overline{CE}$	$\overline{OE}$	BHE	D15/A-1	Data output		Address input	
					D0-D7	D8-D15	LSB	MSB
Standby	H	$\times^{*1}$	$\times$	$\times$	High-Z	High-Z	—	—
Output disable	L	H	$\times$	$\times$	High-Z	High-Z	—	—
Read (16-bit)	L	L	H	Dout	D0 to D7	D8 to D15	A0	A17
Read (8-bit)	L	L	L	L	D0 to D7	High-Z	A-1	A17
Read (8-bit)	L	L	L	H	D8 to D15	High-Z	A-1	A17

Note: 1. $\times$: Don't care.

HN62435 Series

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V_{SS}	V_{CC}	-0.3 to +7.0	V
All input and output voltage relative to V_{SS}	V_{in} , V_{out}	-0.3 to $V_{CC} + 0.3$	V
Operating temperature range	T_{opr}	0 to +70	°C
Storage temperature range	T_{stg}	-55 to +125	°C
Temperature range under bias	T_{bias}	-20 to +85	°C

DC Operating Conditions ($T_a = 0$ to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input high voltage	V_{IH}	2.2	—	$V_{CC} + 0.3$	V
Input low voltage	V_{IL}	-0.3	—	0.8	V

DC Characteristics ($V_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = 0 \text{ V}$, $T_a = 0$ to +70°C)

Parameter	Symbol	Min	Max	Unit	Test conditions
Operating V_{CC} current	I_{CC}	—	50	mA	$V_{CC} = 5.5 \text{ V}$, $I_{DOUT} = 0 \text{ mA}$, $t_{RC} = 120 \text{ ns}$
Standby V_{CC} current	I_{SB1}	—	30	μA	$V_{CC} = 5.5 \text{ V}$, $\overline{CE} \geq V_{CC} - 0.2 \text{ V}$
	I_{SB2}	—	3	mA	$V_{CC} = 5.5 \text{ V}$, $\overline{CE} \geq 2.2 \text{ V}$
Input leakage current	$ I_{IL} $	—	10	μA	$V_{in} = 0$ to V_{CC}
Output leakage current	$ I_{OL} $	—	10	μA	$\overline{CE} = 2.2 \text{ V}$, $V_{OUT} = 0$ to V_{CC}
Output high voltage	V_{OH}	2.4	—	V	$I_{OH} = -205 \text{ μA}$
Output low voltage	V_{OL}	—	0.4	V	$I_{OL} = 1.6 \text{ mA}$

Capacitance ($V_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = 0 \text{ V}$, $T_a = 25^\circ\text{C}$, $V_{in} = 0 \text{ V}$, $f = 1 \text{ MHz}$)

Parameter	Symbol	Min	Max	Unit
Input capacitance	C_{in}	—	10	pF
Output capacitance	C_{out}	—	15	pF

AC Characteristics ($V_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = 0 \text{ V}$, $T_a = 0 \text{ to } +70^\circ\text{C}$)

- Input pulse levels: 0.6 to 2.4 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.5 V
- Output load: 1TTL + $C_L = 100 \text{ pF}$ (including jig)

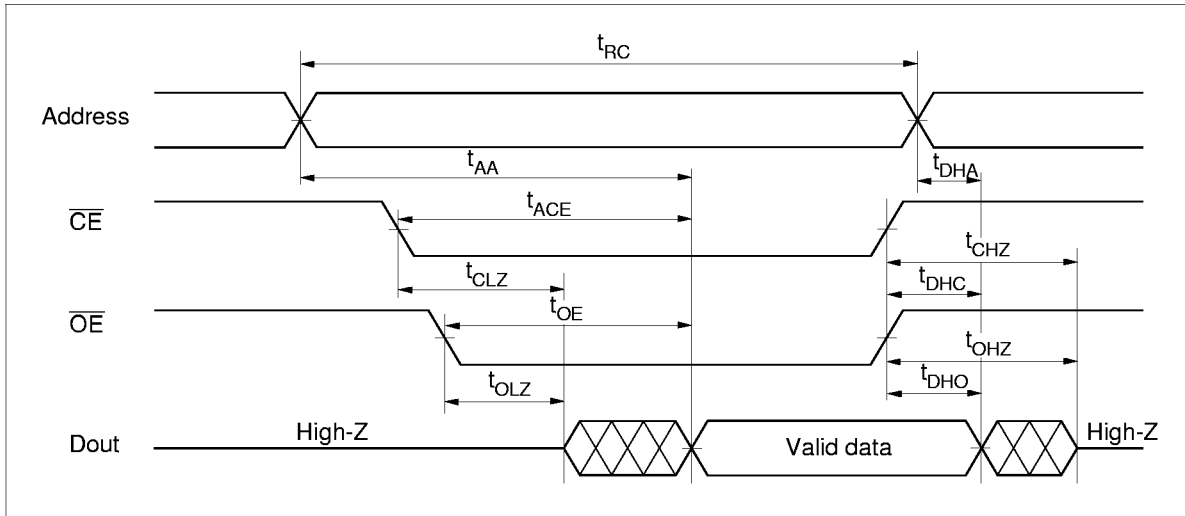
Parameter	Symbol	HN62435-12		Unit	Notes
		Min	Max		
Read cycle time	t_{RC}	120	—	ns	
Address access time	t_{AA}	—	120	ns	3
$\overline{CE}$ access time	t_{ACE}	—	120	ns	3
$\overline{OE}$ access time	t_{OE}	—	60	ns	3
BHE access time	t_{BHE}	—	120	ns	
Output hold time from address change	t_{DHA}	0	—	ns	2
Output hold time from $\overline{CE}$	t_{DHC}	0	—	ns	2
Output hold time from $\overline{OE}$	t_{DHO}	0	—	ns	2
Output hold time from BHE	t_{DHB}	0	—	ns	
$\overline{CE}$ to output in high-Z	t_{CHZ}	—	60	ns	1
$\overline{OE}$ to output in high-Z	t_{OHZ}	—	60	ns	1
BHE to output in high-Z	t_{BHZ}	—	60	ns	1
$\overline{CE}$ to output in low-Z	t_{CLZ}	5	—	ns	4
$\overline{OE}$ to output in low-Z	t_{OLZ}	5	—	ns	4
BHE to output in low-Z	t_{BLZ}	5	—	ns	

- Notes:
1. t_{CHZ} , t_{OHZ} and t_{BHZ} are defined as the time at which the output achieves the open circuit conditions and are not referred to output voltage levels.
 2. t_{DHA} , t_{DHC} , t_{DHO} : Determined by faster.
 3. t_{AA} , t_{ACE} , t_{OE} : Determined by slower.
 4. t_{CLZ} , t_{OLZ} : Determined by slower.
 5. $\overline{CE}$ and $\overline{OE}$ are enable A18 to A0 are valid.
 6. D15/A-1 pin is in the output state when BHE is high, $\overline{CE}$ and $\overline{OE}$ are enable. Therefore, the input signals of opposite phase to the output must be applied to them.
 7. This device is used ATD (Address Transient Detector). Therefore, transfer either $\overline{CE}$ or address (A0 to A17) after power up to 4.5 V.

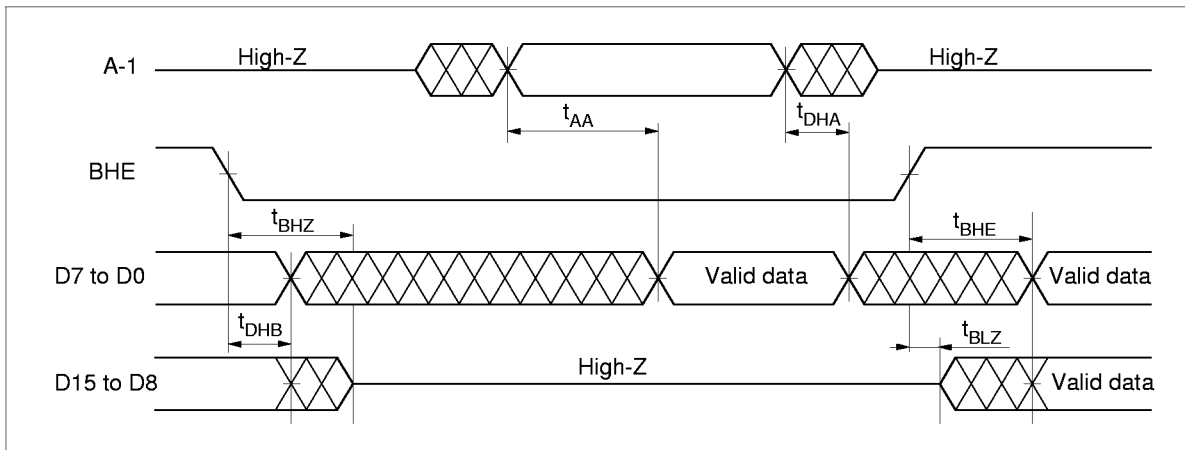
HN62435 Series

Timing Waveforms

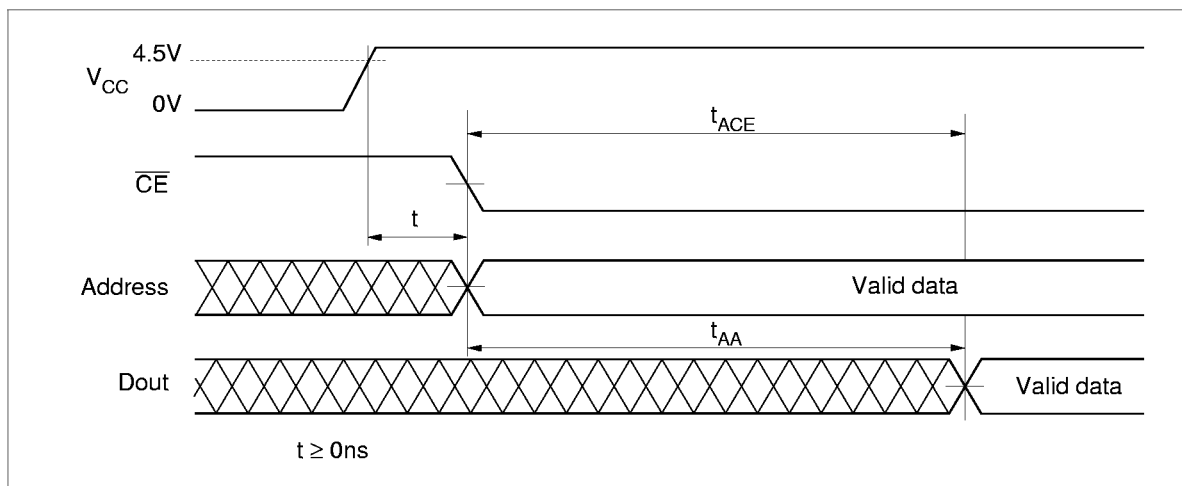
Word Mode (BHE = 'V_{IH}') or Byte Mode (BHE = 'V_{IL}')^{*2, 3, 4}



Word Mode, Byte Mode Switch^{*5, 6}



Power Up Sequence^{*7}

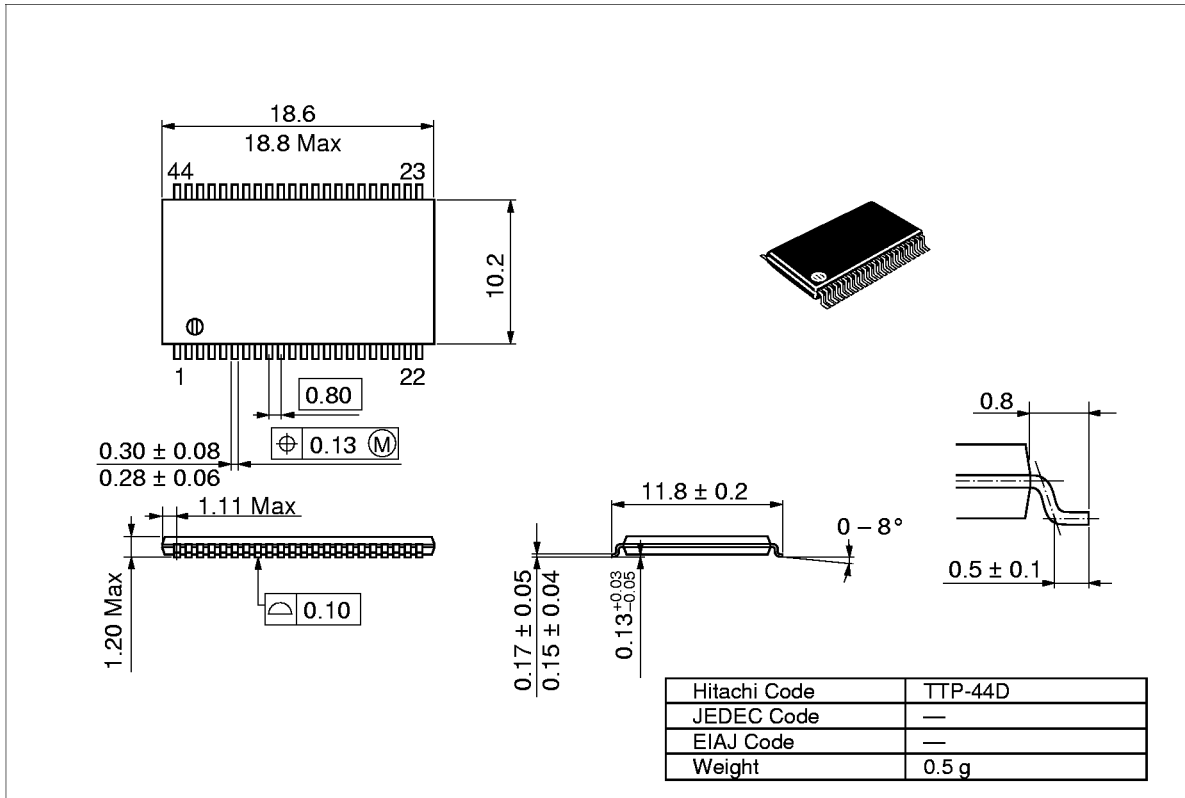


HN62435 Series

Package Dimensions (cont.)

HN62435TT Series (TTP-44D)

Unit: mm



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071

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HN62435 Series

Revision Record

Rev.	Date	Contents of Modification	Drawn by	Approved by
1.0	Nov. 16, 1995	Initial issue	M. Shirai	H. Moriuchi
2.0	Jun. 11, 1997	Change of format Deletion of HN62435-15 Series Operation Table Deletion of Note 2 Capacitance Deletion of Note AC Characteristics Addition of Note 7 Timing Waveforms Addition of Power Up Sequence		
